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cont
- (a) [forming] a gate dielectric over a semiconductor region;
- (b) [forming] a patterned gate over said gate dielectric;
- (c) [then performing] a <sup>p.b.p</sup> lateral growth [step] on said gate dielectric [to increase the thickness of said gate dielectric] at the corners of said gate, but not under central regions of said gate increasing the thickness of said gate dielectric; <sup>pattern</sup>
- (d) [depositing] a unitary electrically conductive metallic material entirely covering [onto sidewalls of] said gate; <sup>pattern</sup>
- (e) reacting said metallic material with said gate to form a conductive compound]; and
- (f) [stripping unreacted portions of said metallic material; whereby a gate structure with enhanced conductivity is formed] source and drain regions in said semiconductor region defining a channel under said patterned gate.

[Amend claim 9 as follows:]

9. (Thrice Amended) A [product produced by the method for forming a] transistor gate structure, comprising [the steps of]:

- (a) [forming] a gate dielectric over a semiconductor region;
- (b) [forming] a patterned gate over said gate dielectric;
- (c) [then performing] a lateral growth [step] on said gate dielectric [to increase the thickness of said gate dielectric] at the corners of said gate, but not under central regions of said gate increasing the thickness of said gate dielectric; and <sup>pattern</sup>
- (d) [after said step (c), forming] a unitary electrically conductive metallic material entirely covering [sidewall spacers on] said gate.

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